

Features

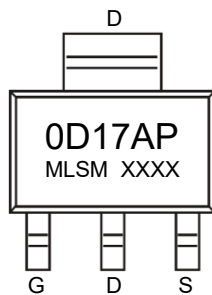
- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-30V	8.5mΩ@10V	-17A
	11.7mΩ@4.5V	

Application

- Battery protection
- Power management
- Load switch

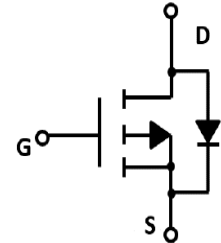


Marking and pin assignment

0D17AP: Device code
XXXX: Code



SOT-223 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		-30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-17	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^{\circ}\text{C}$	-80	A
I_D	Continuous Drain Current@GS=10V	$T_c=25^{\circ}\text{C}$	-17	A
P_D	Maximum Power Dissipation	$T_c=25^{\circ}\text{C}$	1.2	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient(*1 in2 Pad of 2-oz Copper), Max.)		115	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MT0D17AP	SOT-223	0D17AP	2,500	5,000	35,000	13" reel

Electrical Characteristics (T _J =25 °C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25 °C (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-17A	--	8.5	10	mΩ
		V _{GS} =-4.5V, I _D =-10A	--	11.7	14	mΩ
Dynamic Electrical Characteristics @ T _J = 25 °C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	2800	--	pF
C _{OSS}	Output Capacitance		--	350	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	300	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =-15V, I _D =-15A, V _{GS} =-10V	--	30	--	nC
Q _{gs}	Gate Source Charge		--	5.5	--	nC
Q _{gd}	Gate Drain Charge		--	7.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-15V, I _D =-15A, V _{GS} =-10V, R _G =2.5Ω	--	13	--	nS
t _r	Turn-on Rise Time		--	20	--	nS
t _{d(off)}	Turn-Off Delay Time		--	90	--	nS
t _f	Turn-Off Fall Time		--	65	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25 °C, I _S =-17A,	--	--	-1.2	V

Typical Operating Characteristics

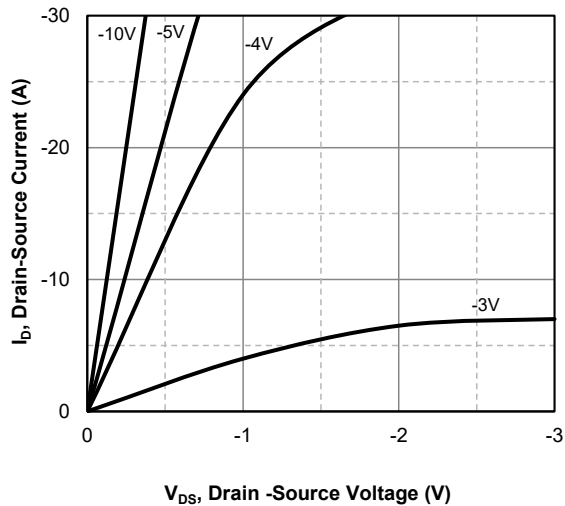


Fig1. Typical Output Characteristics

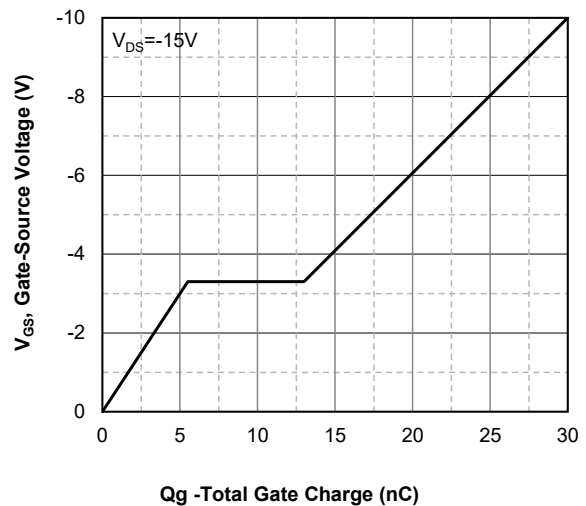


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

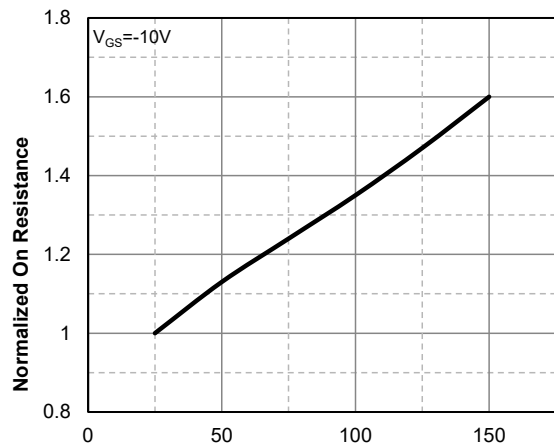


Fig3. Normalized On-Resistance Vs. Temperature

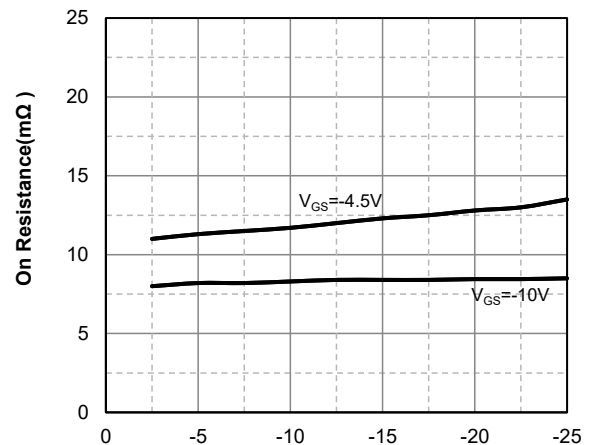


Fig4. On-Resistance Vs. Drain-Source Current

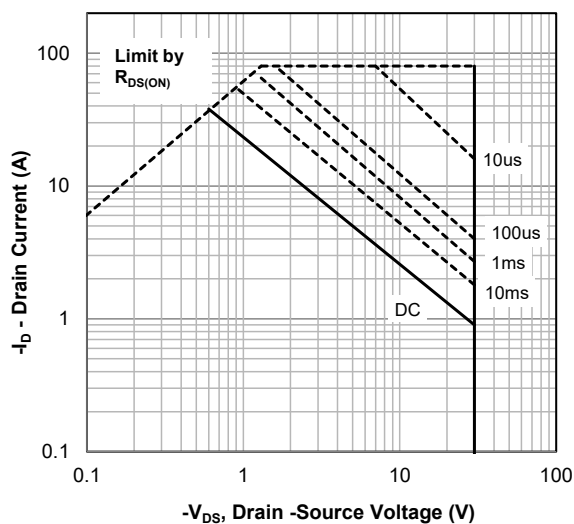


Fig5. Maximum Safe Operating Area

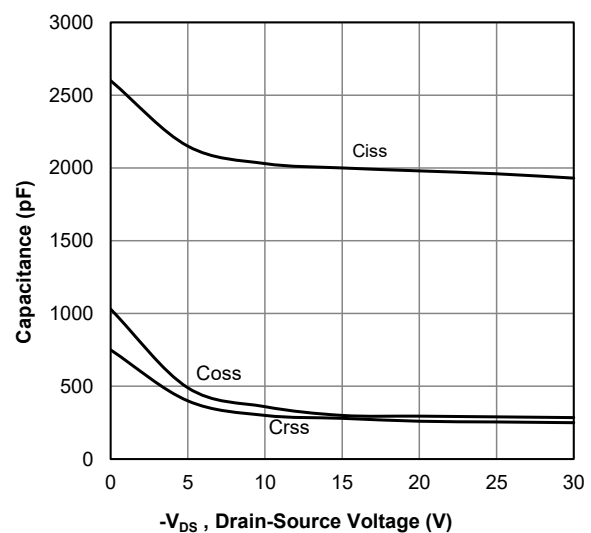
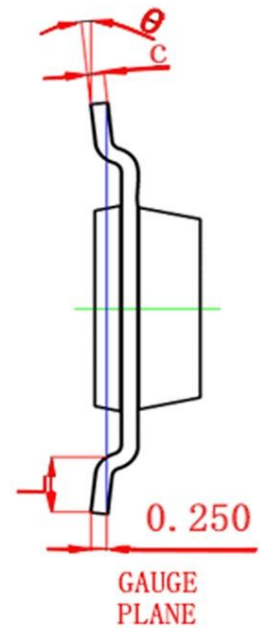
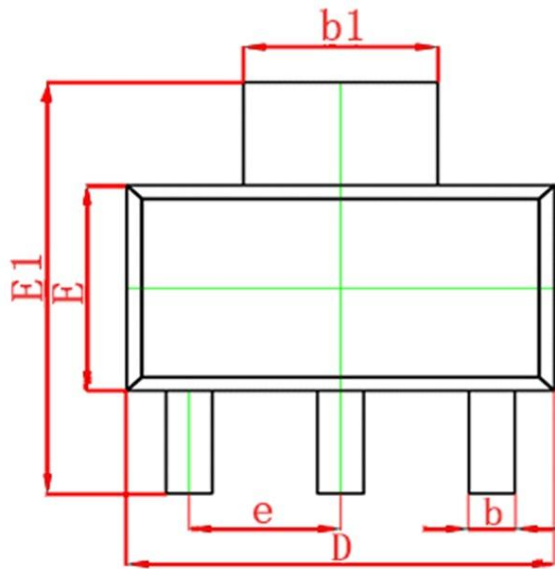


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-223 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	--	1.800	--	0.071
A1	0.020	0.100	0.001	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.840	0.026	0.033
b1	2.900	3.100	0.114	0.122
c	0.230	0.350	0.009	0.014
D	6.300	6.700	0.248	0.264
E	3.300	3.700	0.130	0.146
E1	6.700	7.300	0.264	0.287
e	2.300(BSC)		0.091(BSC)	
L	0.750	--	0.030	--
θ	0°	10°	0°	10°